

Title (en)  
Integrated memory with magnetoresistive memory cells

Title (de)  
Integrierter Speicher mit Speicherzellen mit magnetoresistivem Speichereffekt

Title (fr)  
Mémoire intégrée avec des cellules magnétorésistives

Publication  
**EP 1176605 A3 20020206 (DE)**

Application  
**EP 01113437 A 20010601**

Priority  
DE 10030234 A 20000620

Abstract (en)  
[origin: KR20020000123A] PURPOSE: Integrated memory having memory cells with magnetoresistive memory effect is provided to reduce outlay for repairing the memory in the event of a defect of a memory cell which triggers a short between a row line and a column line. CONSTITUTION: Any known GMR/TMR elements are suitable as the memory cells, provided they exhibit higher impedance than the column lines (BL0 - BLn) and the row lines (WL0 - WLn). The memory here comprises an exemplary number of word lines and bit lines. The memory cells MC, which are arranged in a matrix-type memory cell field(1), are each wired between one of the bit lines BL0 to BLn and one of the word lines (WL0 - WLn).

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IPC 8 full level  
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Citation (search report)  
• [A] DE 19914488 C1 20000531 - SIEMENS AG [DE]  
• [A] US 6054330 A 20000425 - PHIPPS PETER BEVERLEY [US], et al  
• [A] US 4283774 A 19810811 - SCHWARTZ SIDNEY J, et al  
• [A] PATENT ABSTRACTS OF JAPAN vol. 018, no. 658 (E - 1643) 13 December 1994 (1994-12-13)

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